



30V P-Channel Trench Power MOSFET

General Description

The SJJ30P043 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as -4.5V. This device is suitable for use as a wide variety of applications.

Features

- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handling capability
- Lead free product is acquired

Application

- PWM Applications
- Load Switch
- Power Management

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	-30	V
$R_{DS(ON_TYP)}$	4.5	m Ω
I_D	-160	A
Q_G	40	nC



Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJJ30P043	SJJ30P043	TO-263	Tape	\	\	800 Pcs

Table 1. Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	-30	V
V_{GS}	Gate-Source Voltage ($V_{DS}=0V$)	± 20	V
I_D	Drain Current-Continuous($T_C=25^\circ\text{C}$)	-160	A
	Drain Current-Continuous($T_C=100^\circ\text{C}$)	-104	A
I_{DM} (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 1)	-640	A
P_D	Maximum Power Dissipation($T_C=25^\circ\text{C}$)	231	W
	Maximum Power Dissipation($T_C=100^\circ\text{C}$)	93	W
E_{AS}	Avalanche energy (Note 2)	441	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ\text{C}$

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		0.54	$^\circ\text{C/W}$



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Table 3. Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-30V, V_{GS}=0V, T_J=25^\circ\text{C}$			-1	μA
		$V_{DS}=-30V, V_{GS}=0V, T_J=125^\circ\text{C}$			-100	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1		-2.5	V
g_{FS}	Forward Transconductance	$V_{DS}=-5V, I_D=-10A$		41		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS}=-10V, I_D=-20A, T_J=25^\circ\text{C}$		4.5	5.6	m Ω
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS}=-4.5V, I_D=-20A, T_J=25^\circ\text{C}$		6.6	8.8	m Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=-20V, V_{GS}=0V, f=1.0\text{MHz}$		3600		pF
C_{oss}	Output Capacitance			473		pF
C_{rss}	Reverse Transfer Capacitance			370		pF
R_g	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1.0\text{MHz}$		11		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	$V_{GS}=-10V, V_{DS}=-15V, R_L=0.75\Omega, R_{GEN}=6\Omega$		13		nS
t_r	Turn-on Rise Time			115		nS
$t_{d(off)}$	Turn-Off Delay Time			78		nS
t_f	Turn-Off Fall Time			86		nS
Q_g	Total Gate Charge	$V_{GS}=-10V, V_{DS}=-15V, I_D=-20A$		40		nC
Q_{gs}	Gate-Source Charge			7.5		nC
Q_{gd}	Gate-Drain Charge			7.5		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				-160	A
V_{SD}	Forward on Voltage (Note 3)	$V_{GS}=0V, I_S=-20A$			-1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-20A, dI/dt=-100A/\mu s$		13		ns
Q_{rr}	Reverse Recovery Charge	$I_F=-20A, dI/dt=-100A/\mu s$		8		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

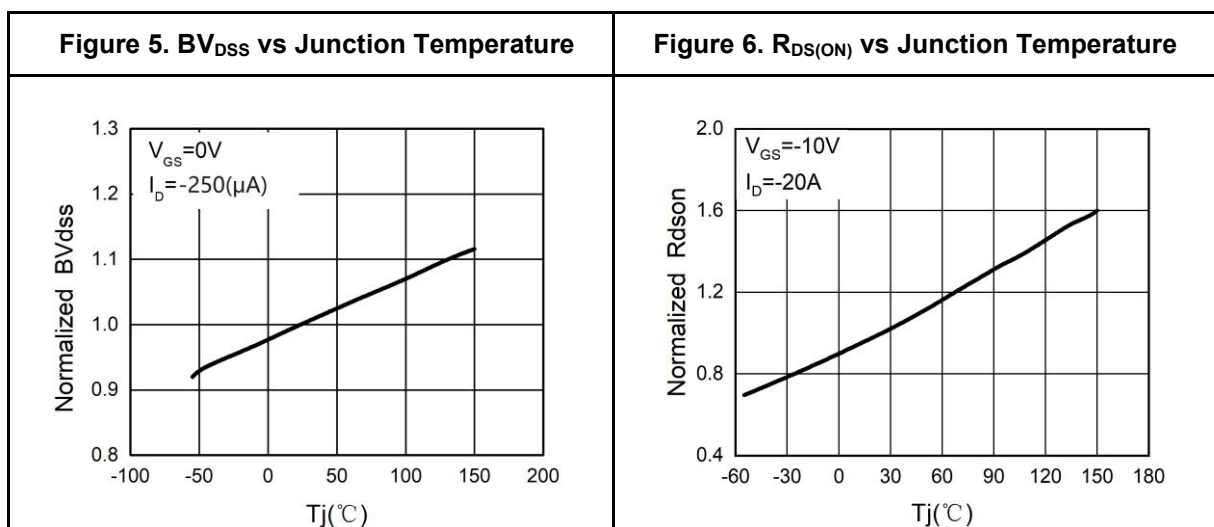
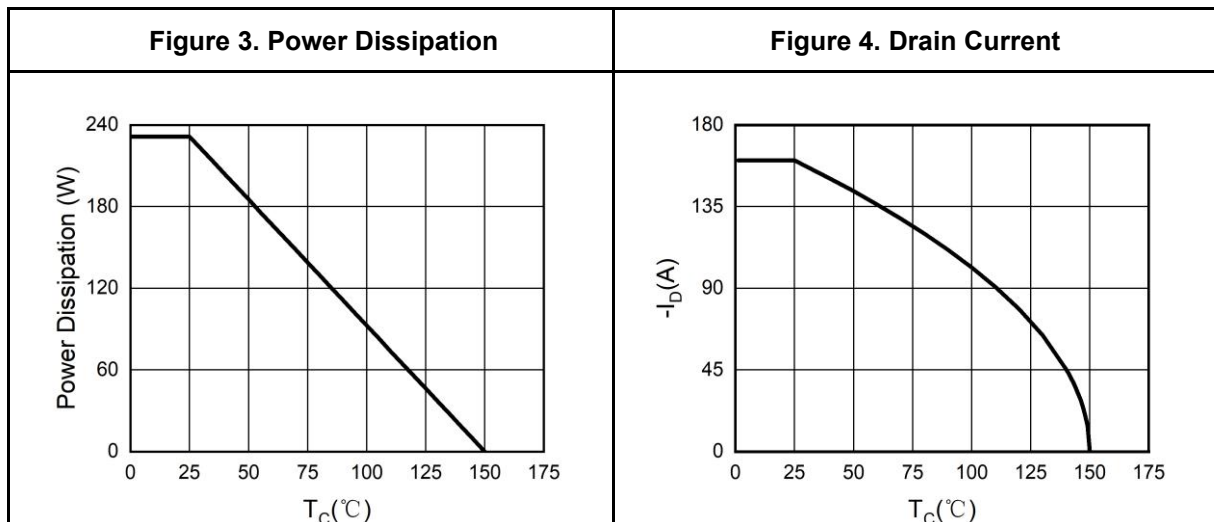
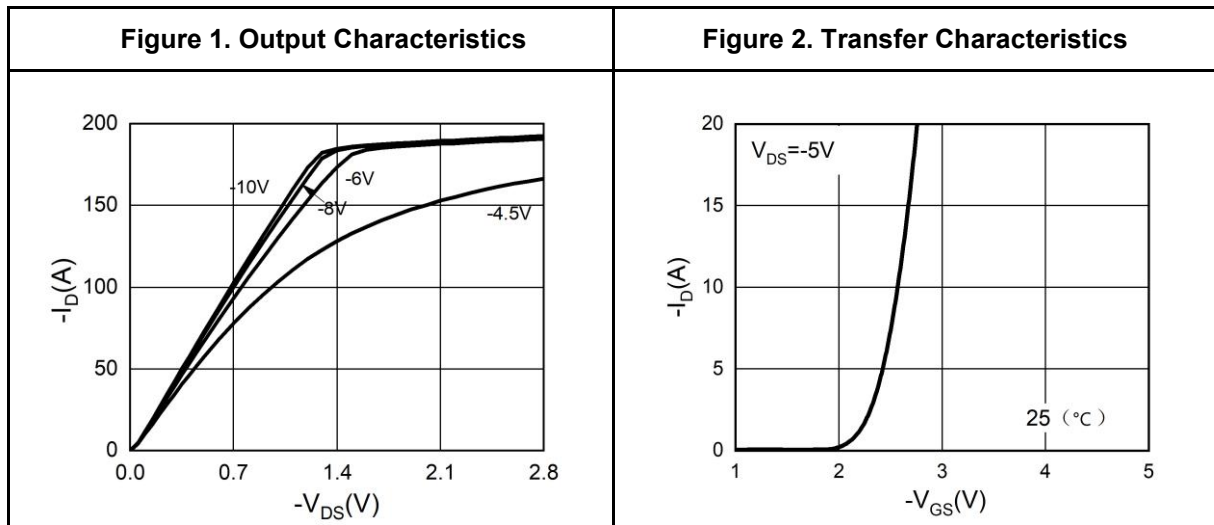
Notes 2.EAS condition: $T_J=25^\circ\text{C}, V_{DD}=-30V, V_G=-10V, R_g=25\Omega, L=0.5\text{mH}$.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



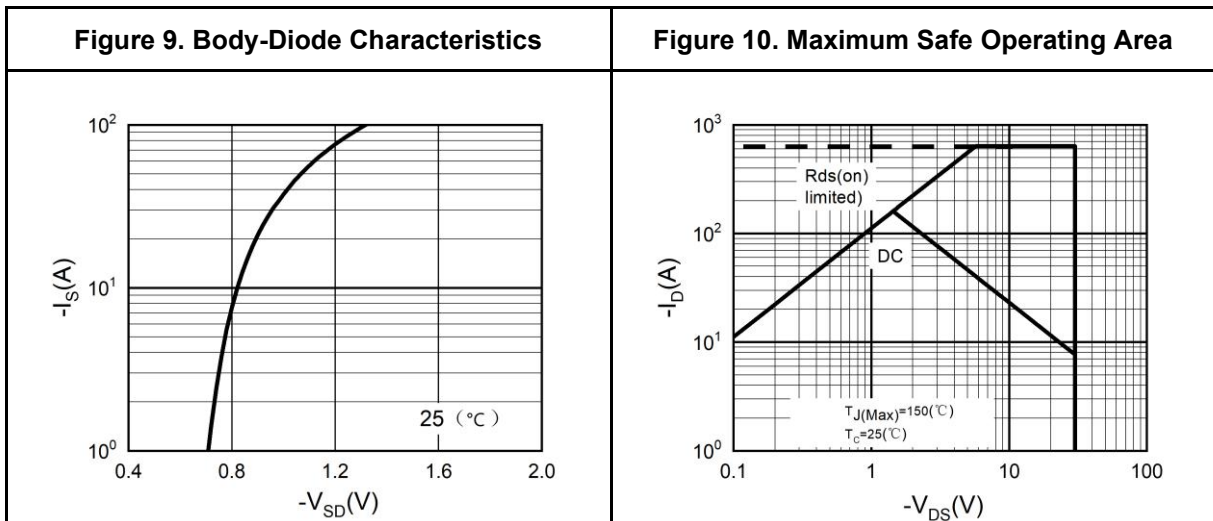
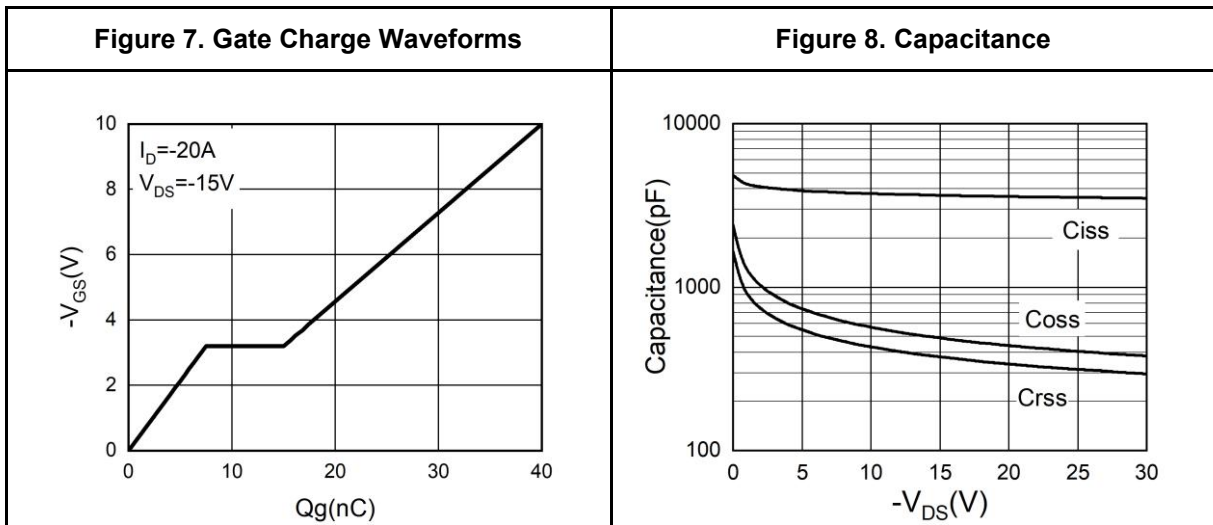
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Typical Electrical And Thermal Characteristics (Curves)





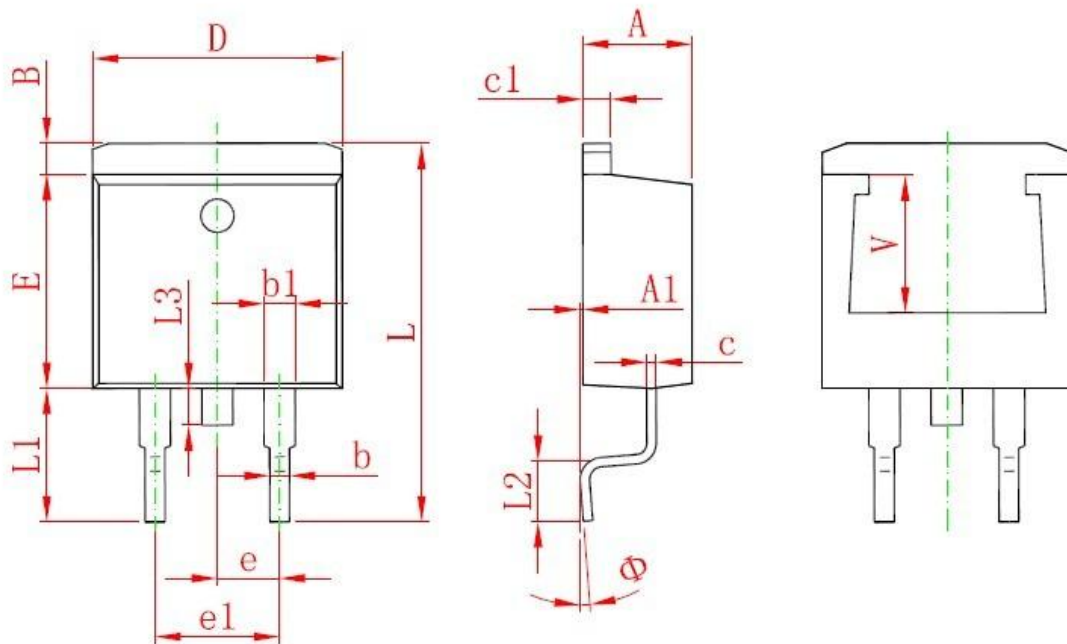
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TO-263 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.120	1.420	0.044	0.056
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100TYP.	
e1	4.980	5.180	0.196	0.204
L	14.940	15.500	0.588	0.610
L1	4.950	5.450	0.195	0.215
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF.		0.220REF.	
Φ	0°	8°	0°	8°



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